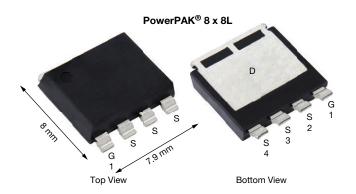


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Vishay Siliconix

Automotive P-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY					
V _{DS} (V)	-40				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.0020				
I _D (A)	-390				
Configuration	Single				
Package	PowerPAK 8 x 8L				

FEATURES

- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Thin 1.6 mm package
- · Very low thermal resistance
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



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PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V _{DS}	-40		
Gate-source voltage	V _{GS}	± 20	V	
Continuous drain current	T _C = 25 °C	1	-390	
	T _C = 125 °C	I _D	-226	
Continuous source current (diode conduction	I _S	545	Α	
Pulsed drain current ^b	I _{DM}	-489		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	66	
Single pulse avalanche energy	L = 0.1 MH	E _{AS}	218	mJ
Maximum power dissipation	T _C = 25 °C	р	600	W
	T _C = 125 °C	P_{D}	200	VV
Operating junction and storage temperature r	T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) d		-	260	-0

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount c	R_{thJA}	44	°C/W
Junction-to-case (drain)		R_{thJC}	0.25	C/VV

Notes

- a. Package limited
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	•				<u>'</u>	'	
Drain-source breakdown voltage	V _{DS}	V_{GS}	= 0, I _D = 250 μA	-40	-	-	.,
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		-2	-2.5	V
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	1	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = -40 V	-	-	1	μΑ
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -40 V, T _J = 125 °C	-	-	200	
		V _{GS} = 0 V	V _{DS} = -40 V, T _J = 175 °C	1	-	330	
On-state drain current a	I _{D(on)}	V _{GS} = -10 V	V _{DS} ≥ -5 V	-100	-	-	Α
	, ,	V _{GS} = -4.5 V	I _D = 8 A	-	0.0020	0.0029	
5		V _{GS} = -10 V	I _D = -10 A	-	0.0014	0.0020	
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = -10 V	I _D = -10 A, T _J = 125 °C	-	-	0.0035	Ω
		V _{GS} = 10 V	I _D = -10 A, T _J = 175 °C	-	-	0.0040	1
Forward transconductance b	9fs	V _{DS} =	15 V, I _D = -50 A	-	180	-	S
Dynamic ^b		•					
Input capacitance	C _{iss}			-	44 421	62 190	
Output capacitance	Coss	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	1633	2287	рF
Reverse transfer capacitance	C _{rss}			-	1476	2067	1
Total gate charge c	Q_g			-	487	731	
Gate-source charge c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = -20 \text{ V}, I_{D} = -30 \text{ A}$	-	89	-	nC
Gate-drain charge c	Q_{gd}			-	82	-	1
Gate resistance	R _q		f = 1 MHz	1.1	2.2	3.3	Ω
Turn-on delay time ^c	t _{d(on)}			-	22	33	
Rise time ^c	t _r	V _{DD} =	$-20 \text{ V, R}_{\text{I}} = 0.67 \Omega$	-	30	45	1
Turn-off delay time c	t _{d(off)}		$I_{D} \cong -30 \text{ A}, V_{GEN} = -10 \text{ V}, R_{g} = 1 \Omega$		196	294	ns ns
Fall time ^c	t _f			-	64	96	
Source-Drain Diode Ratings and Cha	racteristics b	1			L	L	
	ta			-	21	-	
Reverse recovery time	t _b			-	19	-	ns
•	t _{rr}	V _{DD} = -32 V, I _{FM} = -20 A, di/dt = 100 A/μs		-	40	80	1
Reverse recovery charge	Q _{rr}			-	42	84	nC
Reverse recovery current	I _{RM}			-	-	2.0	Α
Pulsed current ^a	I _{SM}			-	_	1100	Α
Forward voltage	V _{SD}	$I_F = -50 \text{ A}, V_{GS} = 0$		_	-0.8	-1.1	V

Notes

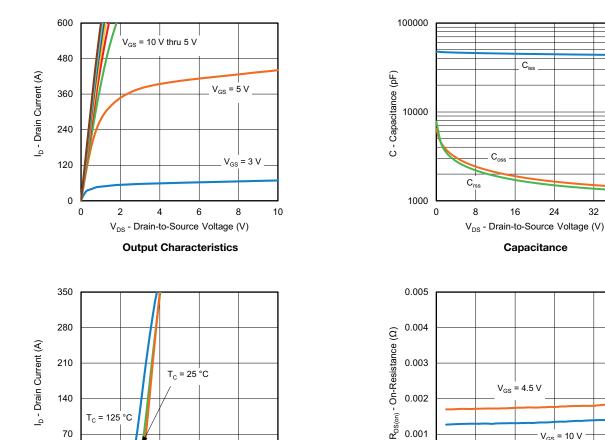
- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

40



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



 V_{GS} - Gate-to-Source Voltage (V) **Transfer Characteristics**

= -55 °C

6

8

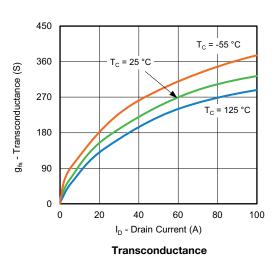
10

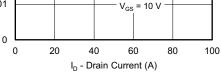
T_C = 125 °C

70

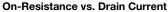
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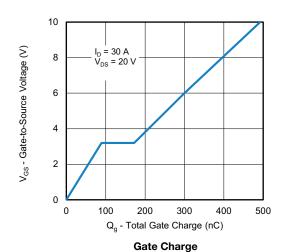
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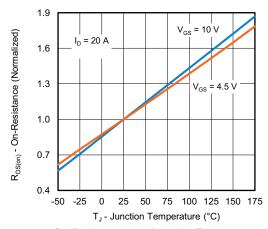
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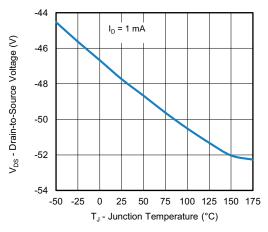




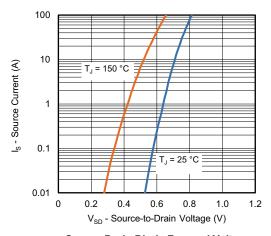
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



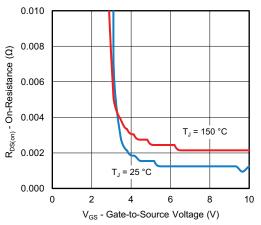
On-Resistance vs. Junction Temperature



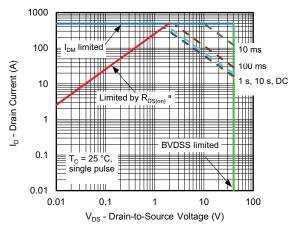
Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage



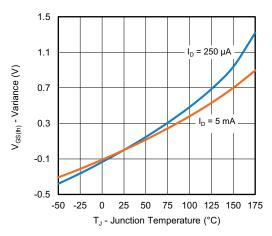
On-Resistance vs. Gate-to-Source Voltage



Safe Operating Area

Note

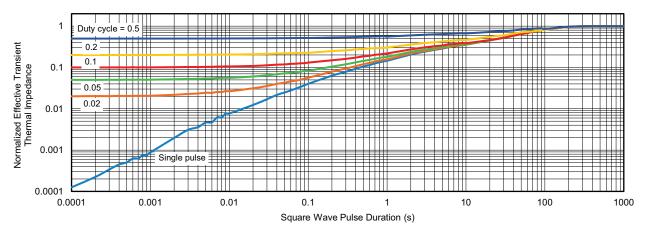
a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified



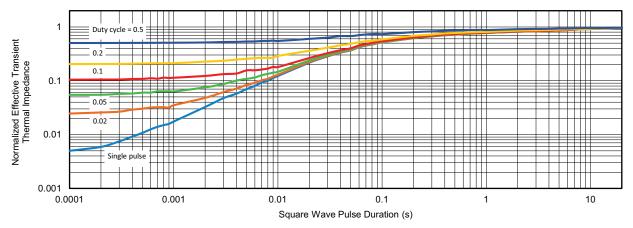
Threshold Voltage



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



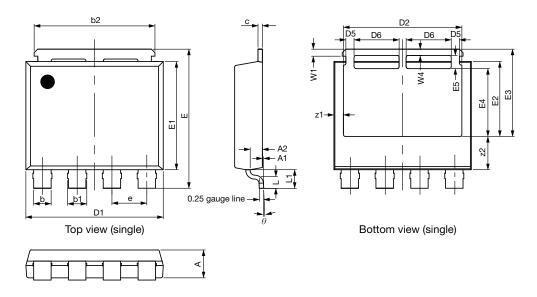
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?77935.



www.vishay.com

PowerPAK® 8 x 8L BWL Case Outline 2



DIM	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	1.50	1.60	1.70	0.059	0.063	0.067	
A1	0.00	-	0.127	0.000	-	0.005	
A2	0.655	0.705	0.755	0.026	0.028	0.030	
b	0.92	1.00	1.08	0.036	0.039	0.043	
b1	1.02	1.10	1.18	0.040	0.043	0.046	
b2	6.84	6.94	7.04	0.269	0.273	0.277	
С	0.20	0.25	0.30	0.008	0.010	0.012	
D1	7.80	7.90	8.00	0.307	0.311	0.315	
D2	6.70	6.80	6.90	0.264	0.268	0.272	
D5	0.37	0.47	0.57	0.015	0.019	0.022	
D6	2.49	2.59	2.69	0.098	0.102	0.106	
е	1.97	2.00	2.03	0.078	0.079	0.080	
E	7.90	8.00	8.10	0.311	0.315	0.319	
E1	6.12	6.22	6.32	0.241	0.245	0.249	
E2	4.21	4.31	4.41	0.166	0.170	0.174	
E3	4.92	5.02	5.12	0.194	0.198	0.202	
E4	3.80	3.90	4.00	0.150	0.154	0.157	
E5	0.65	0.75	0.85	0.026	0.030	0.033	
L	0.61	0.68	0.75	0.024	0.027	0.030	
L1	1.00	1.07	1.15	0.039	0.042	0.045	
W1	0.30	0.40	0.50	0.012	0.016	0.020	
W4	0.32	0.37	0.42	0.013	0.015	0.017	
z1	0.45	0.55	0.65	0.018	0.022	0.026	
z2	1.81	1.91	2.01	0.071	0.075	0.079	
θ	0°	-	5°	0°	-	5°	

ECN: S19-0643-Rev. B, 05-Aug-2019

DWG: 6073

Note

Millimeter will govern

Revison: 05-Aug-2019 1 Document Number: 79736



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